

## **In the Claims**

Claims 1-30 (cancelled).

Claim 31 (original): A method of forming a PMOS device and an NMOS device, comprising:

- providing substrate comprising a PMOS gate region and an NMOS gate region;
- forming a gate dielectric layer over the PMOS and NMOS gate regions of the substrate;
- forming a thick metal-containing material to be over the PMOS gate region and not over the NMOS gate region, the thick metal-containing material being formed to a thickness of greater than 20Å;
- forming a thin metal-containing material to be over the PMOS and NMOS gate regions, the thin metal-containing material being formed to a thickness of less than or equal to about 20Å and being formed over the thick metal-containing material over the PMOS gate region;
- forming a layer of conductively-doped silicon extending across the PMOS and NMOS gate regions and over the thin metal-containing material;
- incorporating the thick metal-containing material, thin metal-containing material and conductively-doped silicon into a PMOS transistor gate stack over the PMOS gate region;
- and
- incorporating the thin metal-containing material and conductively-doped silicon into an NMOS transistor gate stack over the NMOS gate region.

Claim 32 (original): The method of claim 31 wherein the conductively-doped silicon is majority n-type doped.

Claim 33 (original): The method of claim 31 wherein the gate dielectric layer comprises one or more of tantalum, hafnium and aluminum.

Claim 34 (original): The method of claim 31 wherein the gate dielectric layer comprises aluminum oxide over silicon dioxide.

Claim 35 (original): The method of claim 31 wherein the thin metal-containing material comprises one or more of titanium nitride, tantalum nitride, hafnium nitride and tungsten nitride.

Claim 36 (original): The method of claim 31 wherein the thin metal-containing material comprises one or more of titanium silicide, tantalum silicide, hafnium silicide and tungsten silicide.

Claim 37 (original): The method of claim 31 wherein the metal of the thin metal-containing material predominately comprises one or more of titanium, tantalum, tungsten and hafnium.

Claim 38 (original): The method of claim 31 wherein the thickness of the thin metal-containing material is less than or equal to about 15Å.

Claim 39 (original): The method of claim 31 wherein the thickness of the thin metal-containing material is than or equal to about 10Å.

Claim 40 (original): A method of forming a capacitor construction, comprising:

- forming a dielectric layer over a capacitor storage node;
- forming a metal-containing material over the dielectric layer, the metal-containing material being formed with less than or equal to about 70 ALD cycles; and
- forming conductively-doped silicon over the metal-containing material.

Claim 41 (original): The method of claim 40 wherein the conductively-doped silicon is majority n-type doped.

Claim 42 (original): The method of claim 40 wherein the dielectric layer comprises one or more of tantalum, hafnium and aluminum.

Claim 43 (original): The method of claim 40 wherein the metal-containing material comprises one or more of titanium nitride, tantalum nitride, hafnium nitride and tungsten nitride.

Claim 44 (original): The method of claim 40 wherein the metal-containing material comprises one or more of titanium silicide, tantalum silicide, hafnium silicide and tungsten silicide.

Claim 45 (original): The method of claim 40 wherein the metal of the metal-containing material predominately comprises one or more of titanium, tantalum, hafnium and tungsten.

Claim 46 (original): The method of claim 40 wherein the metal-containing material has a thickness of less than or equal to about 20Å.

Claim 47 (original): The method of claim 40 wherein the metal-containing material has a thickness of less than or equal to about 15Å.

Claim 48 (original): The method of claim 40 wherein the metal-containing material has a thickness of less than or equal to about 10Å.

Claim 49 (original): A method of forming a capacitor construction, comprising:  
forming a capacitor electrode comprising conductively-doped silicon; and  
providing a metal-containing material between the capacitor electrode and a capacitor dielectric layer, the metal-containing material having a thickness of no more than about 20Å.

Claim 50 (original): The method of claim 49 wherein the conductively-doped silicon is majority n-type doped.

Claim 51 (original): The method of claim 49 wherein the dielectric layer comprises one or more of tantalum, hafnium and aluminum.

Claim 52 (original): The method of claim 49 wherein the dielectric layer comprises aluminum oxide.

Claim 53 (original): The method of claim 49 wherein the metal of the metal-containing material predominately comprises one or more of titanium, tantalum, hafnium and tungsten.

Claim 54 (original): The method of claim 49 wherein the metal-containing material comprises one or more of titanium nitride, tantalum nitride, hafnium nitride and tungsten nitride.

Claim 55 (original): The method of claim 49 wherein the metal-containing material comprises one or more of titanium silicide, tantalum silicide, hafnium silicide and tungsten silicide.

Claim 56 (original): The method of claim 49 wherein the thickness of the metal-containing material is less than or equal to about 15Å.

Claim 57 (original): The method of claim 49 wherein the thickness of the metal-containing material is less than or equal to about 10Å.

Claims 58-94 (cancelled).